TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSVI-H)

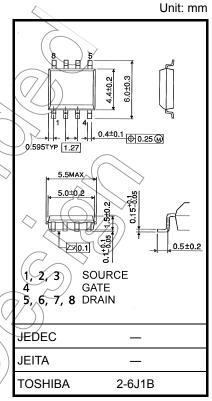
# **TPC8040-H**

High Efficiency DC-DC Converter Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: QSW = 5.1 nC (typ.)
- Low drain-source ON-resistance: RDS (ON) =  $6.4 \text{ m}\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 48 \text{ S (typ.)}$
- Low leakage current:  $I_{DSS} = 10 \mu A (max) (V_{DS} = 30 V)$
- Enhancement mode:  $V_{th} = 1.3$  to 2.3 V ( $V_{DS} = 10$  V,  $I_{D} = 0.2$  mA)

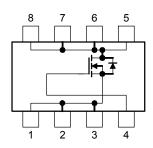
## Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	30	V
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		V <sub>DGR</sub>	30	V
Gate-source voltage		V <sub>GSS</sub>	±20	< <u>\</u>
Drain current	DC (Note 1)	ID( (	13	A
	Pulsed (Note 1)	DEP.	52	, ^
Drain power dissipation (t = 10 s) (Note 2a)		PD	1.9	/w
Drain power dissipation (t = 10 s) (Note 2b)		D	1.0	∑w
Single pulse avalanche energy (Note 3)		EAS	110	mJ
Avalanche current		IAR	13	Α
Repetitive avalanche energy (Note 2a) (Note 4)		EAR	2.0	mJ
Channel temperature		₹ <sup>T</sup> ch	150	°C
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C
	/ />			



Weight: 0.085 g (typ.)

### **Circuit Configuration**



Note: For Notes 1 to 4, refer to the next page.

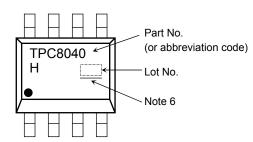
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating" Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.

#### **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2a)	R <sub>th (ch-a)</sub>	65.8	°C/W
Thermal resistance, channel to ambient $(t=10 \; s) \eqno (Note \; 2b)$	R <sub>th (ch-a)</sub>	125	°C/W

### Marking (Note 5)



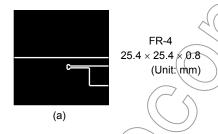
Note 6: A line under a Lot No. identifies the indication of product Labels [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

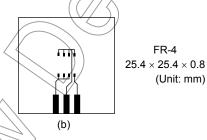
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Note 1: Ensure that the channel temperature does not exceed 150°C

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)





Note 3:  $V_{DD} = 24 \text{ V}$ ,  $T_{Ch} = 25^{\circ}\text{C}$  (initial),  $L = 500 \mu\text{H}$ ,  $R_G = 25 \Omega$ ,  $L_{AR} = 13 \text{ A}$ 

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: • on lower left of the marking indicates Pin 1:

\* Weekly code: (Three digits)

Week of manufacture

(0) for the first week of the year: sequential number up to 52 or 53)

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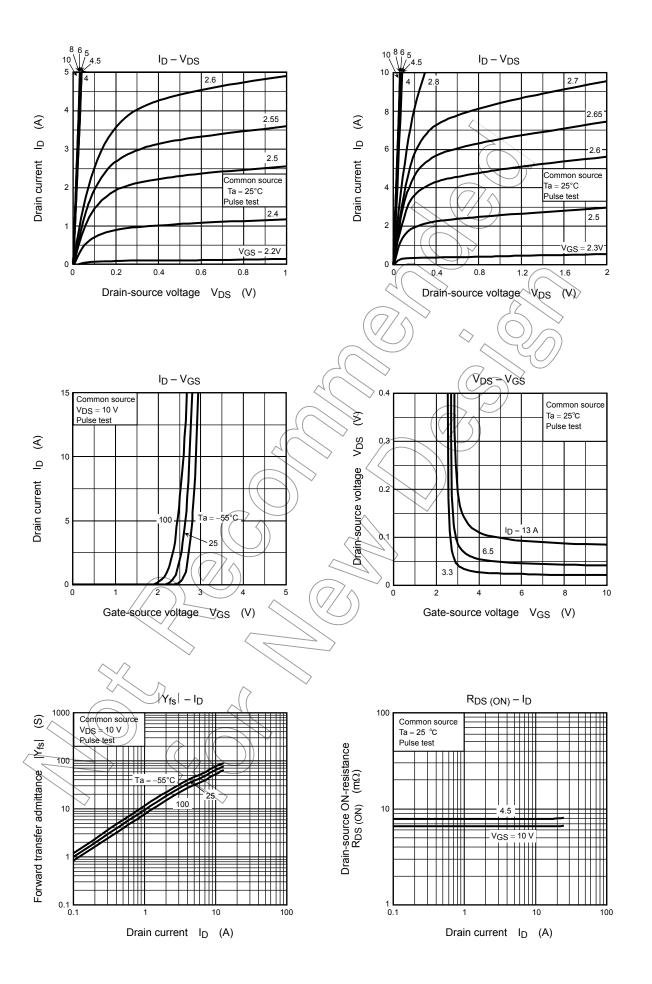
Year of manufacture (The last digit of the year)

## **Electrical Characteristics (Ta = 25°C)**

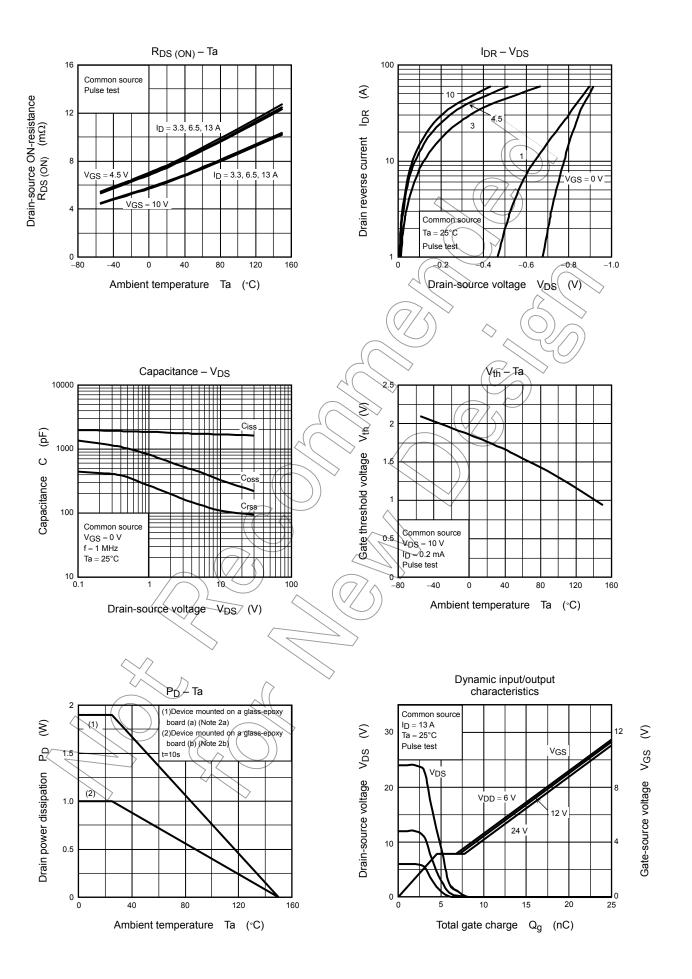
Cha	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage curr	rent	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA
Drain cutoff curre	nt	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V	_	_	10	μΑ
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_	_	V
		V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15	_	_	V
Gate threshold vo	ltage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, I_D = 0.2 \text{ mA}$	1.3	) >-	2.3	V
Drain-source ON-resistance		Б	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 6.5 A	$\rightarrow$	7.7	11.1	- mΩ
		R <sub>DS</sub> (ON)	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 6.5 A	))	6.4	9.7	
Forward transfer a	admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 7 A	24	48	_	S
Input capacitance		C <sub>iss</sub>		_	1700	2200	
Reverse transfer	capacitance	C <sub>rss</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	110	170	pF
Output capacitano	ce	C <sub>oss</sub>			330	$\searrow$	
Gate resistance		rg	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 5 MHz	-	2.3	> 3.5	Ω
Switching time	Rise time	t <sub>r</sub>	V <sub>GS</sub> 10 V I <sub>D</sub> = 6.5 A V <sub>OUT</sub>		5.5	) —	
	Turn-on time	t <sub>on</sub>		7	15	_	ne
	Fall time	t <sub>f</sub>	B = 2.		8.6	_	ns
	Turn-off time	t <sub>off</sub>	V <sub>DD</sub> ≈ 15 V Duty ≤ 1%, t <sub>w</sub> ≠ 10 μs	_	39	_	
Total gate charge (gate-source plus gate-drain)		Qg	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 13 \text{ A}$	_	24	_	
			$V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 13 \text{ A}$	_	12	_	
Gate-source char	ge 1 /	Q <sub>ĝs1</sub>		_	4.6	_	nC
Gate-drain ("miller") charge		Qgd	$V_{DD} \approx 24 V$ , $V_{GS} = 10 V$ , $I_{D} = 13 A$	_	3.2	_	
Gate switch charg	ge (7)	Q <sub>SW</sub>		_	5.1	_	

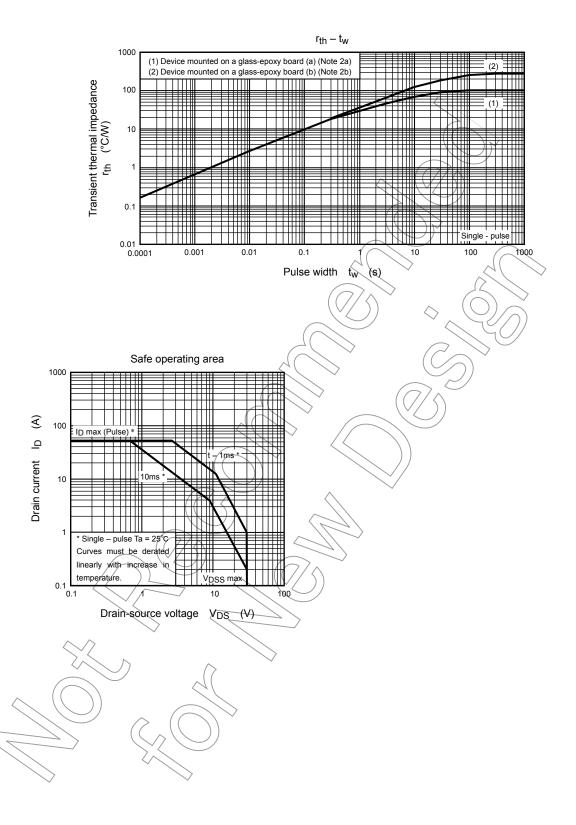
## Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol Test Condition	Min	Тур.	Max	Unit
Drain reverse current Pulse (Note 1)	I <sub>DRP</sub> —	_	_	52	Α
Forward voltage (diode)	V <sub>DSF</sub> I <sub>DR</sub> = 13 A, V <sub>GS</sub> = 0 V	_	_	-1.2	V



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